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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	668-BBGA Exposed Pad
Supplier Device Package	668-PBGA-PGE (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmc8358eczqagdda

  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
  - System initialization data is optionally loaded from I^2C-1 EPROM by boot sequencer embedded hardware
- DMA controller
  - Four independent virtual channels
  - Concurrent execution across multiple channels with programmable bandwidth control
  - All channels accessible by local core and remote PCI masters
  - Misaligned transfer capability
  - Data chaining and direct mode
  - Interrupt on completed segment and chain
  - DMA external handshake signals: $\overline{\text{DMA\_DREQ}}$[0:3]/$\overline{\text{DMA\_DACK}}$[0:3]/$\overline{\text{DMA\_DONE}}$[0:3]. There is one set for each DMA channel. The pins are multiplexed to the parallel IO pins with other QE functions.
- DUART
  - Two 4-wire interfaces (RxD, TxD, RTS, CTS)
  - Programming model compatible with the original 16450 UART and the PC16550D
- System timers
  - Periodic interrupt timer
  - Real-time clock
  - Software watchdog timer
  - Eight general-purpose timers
- IEEE Std. 1149.1™-compliant, JTAG boundary scan
- Integrated PCI bus and SDRAM clock generation

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8358E. The device is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1.2 Power Supply Voltage Specification

Table 2 provides the recommended operating conditions for the device. Note that the values in Table 2 are the recommended and tested operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic	Symbol	Recommended Value	Unit	Notes
Core supply voltage	V_{DD}	1.2 V ± 60 mV	V	1
PLL supply voltage	AV_{DD}	1.2 V ± 60 mV	V	1
DDR and DDR2 DRAM I/O supply voltage DDR DDR2	GV_{DD}	 2.5 V ± 125 mV 1.8 V ± 90 mV	V	—
Three-speed Ethernet I/O supply voltage	$LV_{DD}0$	3.3 V ± 330 mV 2.5 V ± 125 mV	V	—
Three-speed Ethernet I/O supply voltage	$LV_{DD}1$	3.3 V ± 330 mV 2.5 V ± 125 mV	V	—
Three-speed Ethernet I/O supply voltage	$LV_{DD}2$	3.3 V ± 330 mV 2.5 V ± 125 mV	V	—
PCI, local bus, DUART, system control and power management, I^2C, SPI, and JTAG I/O voltage	OV_{DD}	3.3 V ± 330 mV	V	—
Junction temperature	T_J	0 to 105 –40 to 105	°C	—

Notes:
1. GV_{DD}, LV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.

Table 13. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V (continued)

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input current (0 V ≤ V_{IN} ≤ OV_{DD})	I_{IN}	—	±10	μA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to equal 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} cannot exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to equal MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

Table 14 provides the DDR2 capacitance when GV_{DD}(typ) = 1.8 V.

Table 14. DDR2 SDRAM Capacitance for GV_{DD}(typ)=1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.090 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 15 provides the recommended operating conditions for the DDR SDRAM component(s) of the device when GV_{DD}(typ) = 2.5 V.

Table 15. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	GV_{DD}	2.375	2.625	V	1
I/O reference voltage	MV_{REF}	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MV_{REF} – 0.04	MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	MV_{REF} + 0.18	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MV_{REF} – 0.18	V	—
Output leakage current	I_{OZ}	—	±10	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–15.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	15.2	—	mA	—
MV_{REF} input leakage current	I_{VREF}	—	±10	μA	—
Input current (0 V ≤ V_{IN} ≤ OV_{DD})	I_{IN}	—	±10	μA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8358E.

7.1 DUART DC Electrical Characteristics

Table 22 provides the DC electrical characteristics for the DUART interface of the device.

Table 22. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V	—
Low-level input voltage OV_{DD}	V_{IL}	–0.3	0.8	V	—
High-level output voltage, I_{OH} = –100 µA	V_{OH}	OV_{DD} – 0.4	—	V	—
Low-level output voltage, I_{OL} = 100 µA	V_{OL}	—	0.2	V	—
Input current (0 V ≤V_{IN} ≤ OV_{DD})	I_{IN}	—	±10	µA	1

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

7.2 DUART AC Electrical Specifications

Table 23 provides the AC timing parameters for the DUART interface of the device.

Table 23. DUART AC Timing Specifications

Parameter	Value	Unit	Notes
Minimum baud rate	256	baud	—
Maximum baud rate	>1,000,000	baud	1
Oversample rate	16	—	2

Notes:
1. Actual attainable baud rate will be limited by the latency of interrupt processing.
2. The middle of a start bit is detected as the eighth sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each sixteenth sample.

8 UCC Ethernet Controller: Three-Speed Ethernet, MII Management

This section provides the AC and DC electrical characteristics for three-speed, 10/100/1000, and MII management.

Figure 13 shows the MII receive AC timing diagram.

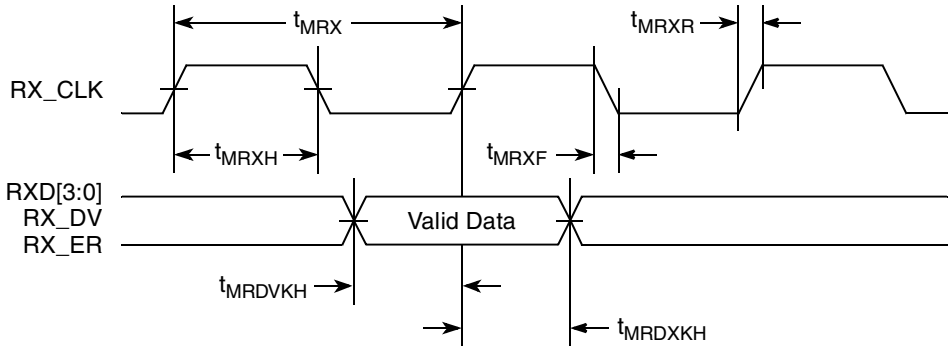


Figure 13. MII Receive AC Timing Diagram

8.2.3 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

8.2.3.1 RMII Transmit AC Timing Specifications

Table 30 provides the RMII transmit AC timing specifications.

Table 30. RMII Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
REF_CLK clock	t_{RMX}	—	20	—	ns
REF_CLK duty cycle	t_{RMXH}/t_{RMX}	35	—	65	%
REF_CLK to RMII data TXD[1:0], TX_EN delay	$t_{RMTKHDX}$ $t_{RMTKHDV}$	2 —	—	— 10	ns
REF_CLK data clock rise time	t_{RMXR}	1.0	—	4.0	ns
REF_CLK data clock fall time	t_{RMXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first three letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{RMTKHDX}$ symbolizes RMII transmit timing (RMT) for the time t_{RMX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII(RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Table 34. RGMII and RTBI AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD} of 2.5 V ± 5%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
GTX_CLK125 reference clock duty cycle	t_{G125H}/t_{G125}	47	—	53	%	—

Notes:

1. Note that, in general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (Rx) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).
2. This implies that PC board design will require clocks to be routed such that an additional trace delay of greater than 1.5 ns will be added to the associated clock signal.
3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned between.
5. Duty cycle reference is $LV_{DD}/2$.
6. This symbol is used to represent the external GTX_CLK125 and does not follow the original symbol naming convention.
7. In rev. 2.1 silicon, due to errata, $t_{SKRGTKHDX}$ minimum is –0.65 ns for UCC2 option 1 and –0.9 for UCC2 option 2, and $t_{SKRGTKHDV}$ maximum is 0.75 ns for UCC1 and UCC2 option 1 and 0.85 for UCC2 option 2. UCC1 does meet $t_{SKRGTKHDX}$ minimum for rev. 2.1 silicon.

Figure 19 shows the RGMII and RTBI AC timing and multiplexing diagrams.

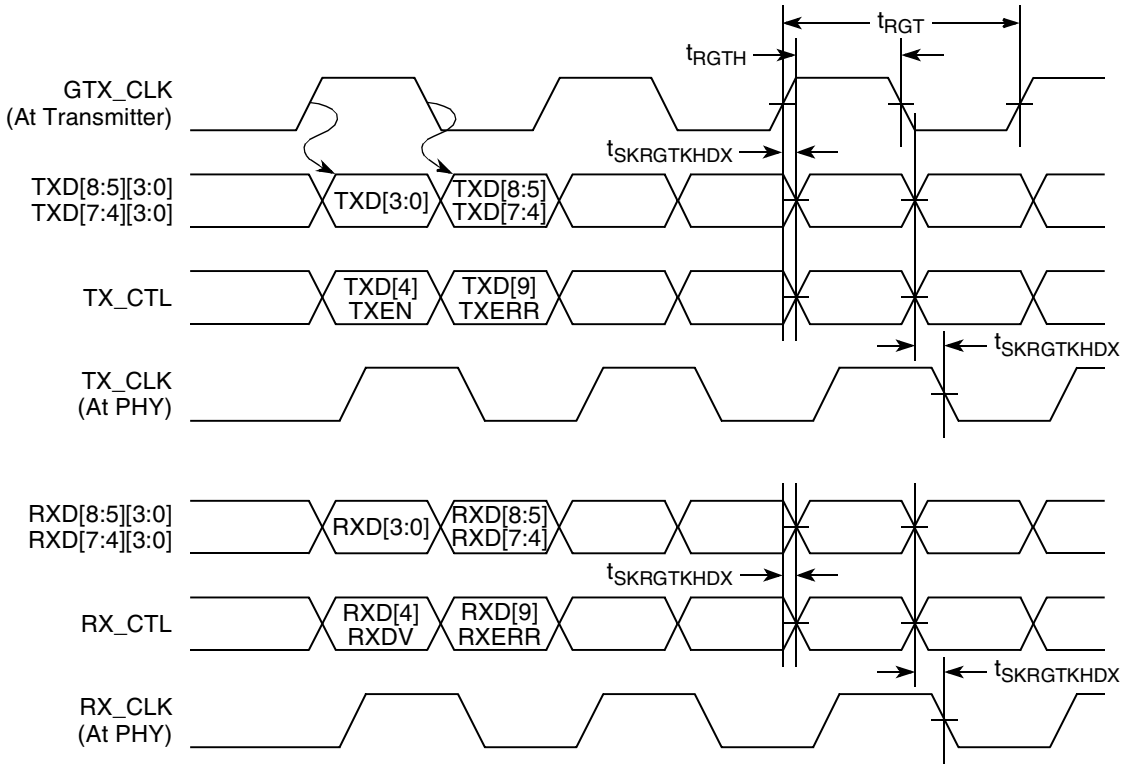


Figure 19. RGMII and RTBI AC Timing and Multiplexing Diagrams

Table 36. MII Management AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD} is 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
MDC fall time	t_{MDHF}	—	—	10	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, $t_{MDRDVKH}$ symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the csb_clk speed (that is, for a csb_clk of 267 MHz, the maximum frequency is 8.3 MHz and the minimum frequency is 1.2 MHz; for a csb_clk of 375 MHz, the maximum frequency is 11.7 MHz and the minimum frequency is 1.7 MHz).
3. This parameter is dependent on the ce_clk speed (that is, for a ce_clk of 200 MHz, the delay is 90 ns and for a ce_clk of 300 MHz, the delay is 63 ns).

Figure 20 shows the MII management AC timing diagram.

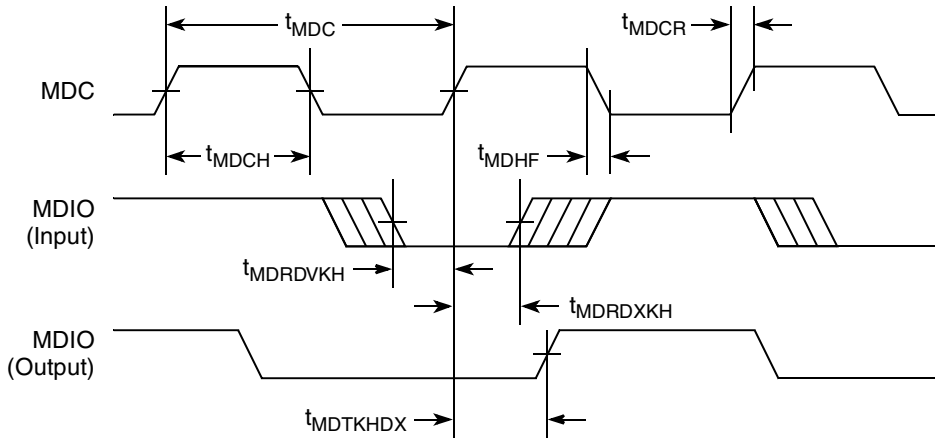


Figure 20. MII Management Interface Timing Diagram

8.3.3 IEEE 1588 Timer AC Specifications

Table 37 provides the IEEE 1588 timer AC specifications.

Table 37. IEEE 1588 Timer AC Specifications

Parameter	Symbol	Min	Max	Unit	Notes
Timer clock frequency	t_{TMRCK}	0	70	MHz	1
Input setup to timer clock	t_{TMRCKS}	—	—	—	2, 3
Input hold from timer clock	t_{TMRCKH}	—	—	—	2, 3
Output clock to output valid	t_{GCLKNV}	0	6	ns	—

Table 39. Local Bus General Timing Parameters—DLL Enabled (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus clock to LALE rise	t_{LBKHLR}	—	4.5	ns	—
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	4.5	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	4.5	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	4.5	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	1.0	—	ns	3
Output hold from local bus clock for LAD/LDP	$t_{LBKHOX2}$	1.0	—	ns	3
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	3.8	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to rising edge of LSYNC_IN.
3. All signals are measured from $OV_{DD}/2$ of the rising edge of LSYNC_IN to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when RCWH[LALE] is not set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
6. $t_{LBOTOT2}$ should be used when RCWH[LALE] is set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
7. $t_{LBOTOT3}$ should be used when RCWH[LALE] is set and when the load on LALE output pin equals to the load on LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

Table 40 describes the general timing parameters of the local bus interface of the device.

Table 40. Local Bus General Timing Parameters—DLL Bypass Mode

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	15	—	ns	2
Input setup to local bus clock	t_{LBIVKH}	7	—	ns	3, 4
Input hold from local bus clock	t_{LBIXKH}	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7
Local bus clock to output valid	t_{LBKHOV}	—	3	ns	3

Table 40. Local Bus General Timing Parameters—DLL Bypass Mode (continued)

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus clock to output high impedance for LAD/LDP	t_{LBKHOZ}	—	4	ns	—

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to falling edge of LCLK0 (for all outputs and for $\overline{\text{LGTA}}$ and LUPWAIT inputs) or rising edge of LCLK0 (for all other inputs).
3. All signals are measured from $OV_{DD}/2$ of the rising/falling edge of LCLK0 to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. $t_{LBOTOT1}$ should be used when RCWH[LALE] is not set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
6. $t_{LBOTOT2}$ should be used when RCWH[LALE] is set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
7. $t_{LBOTOT3}$ should be used when RCWH[LALE] is set and when the load on LALE output pin equals to the load on LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
9. DLL bypass mode is not recommended for use at frequencies above 66 MHz.

Figure 21 provides the AC test load for the local bus.

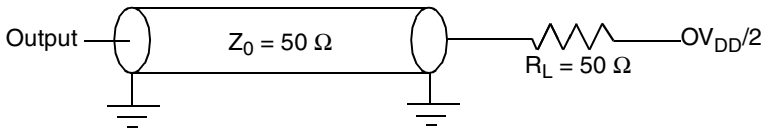


Figure 21. Local Bus C Test Load

Table 44. I²C AC Electrical Specifications (continued)

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 43).

Parameter	Symbol[1]	Min	Max	Unit
Data hold time: CBUS compatible masters I²C bus devices	t_{I2DXKL}	 — 0[2]	 — 0.9[3]	µs
Rise time of both SDA and SCL signals	t_{I2CR}	20 + 0.1 C_b[4]	300	ns
Fall time of both SDA and SCL signals	t_{I2CF}	20 + 0.1 C_b[4]	300	ns
Set-up time for STOP condition	t_{I2PVKH}	0.6	—	µs
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	µs
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	0.1 × OV_{DD}	—	V
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	0.2 × OV_{DD}	—	V

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{I2DVKH} symbolizes I²C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I²C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I²C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. The device provides a hold time of at least 300 ns for the SDA signal (referred to the V_{IH} min of the SCL signal) to bridge the undefined region of the falling edge of SCL.
3. The maximum t_{I2DVKH} has only to be met if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. C_B = capacitance of one bus line in pF.

Figure 33 provides the AC test load for the I²C.

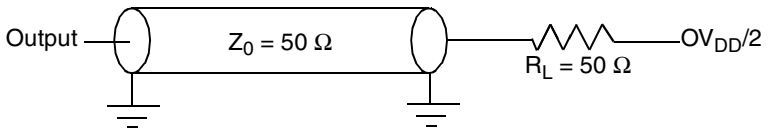


Figure 33. I²C AC Test Load

Figure 34 shows the AC timing diagram for the I²C bus.

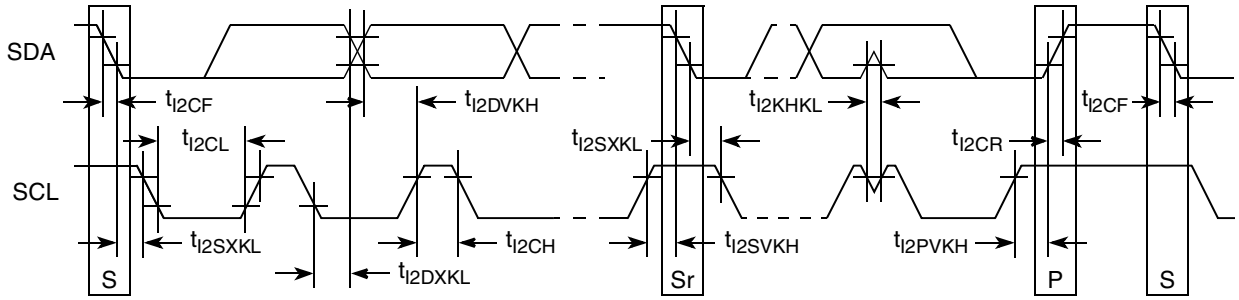


Figure 34. I²C Bus AC Timing Diagram

16.1 SPI DC Electrical Characteristics

Table 54 provides the DC electrical characteristics for the device SPI.

Table 54. SPI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V ≤ V_{IN} ≤ OV_{DD}	—	±10	μA

16.2 SPI AC Timing Specifications

Table 55 and provide the SPI input and output AC timing specifications.

Table 55. SPI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
SPI outputs—Master mode (internal clock) delay	t_{NIKHOX} t_{NIKHOV}	0.4 —	— 8	ns
SPI outputs—Slave mode (external clock) delay	t_{NEKHOX} t_{NEKHOV}	2 —	— 8	ns
SPI inputs—Master mode (internal clock) input setup time	t_{NIIVKH}	8	—	ns
SPI inputs—Master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOV} symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).

Figure 40 provides the AC test load for the SPI.

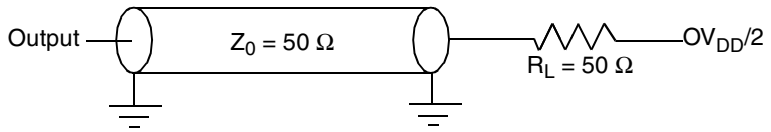
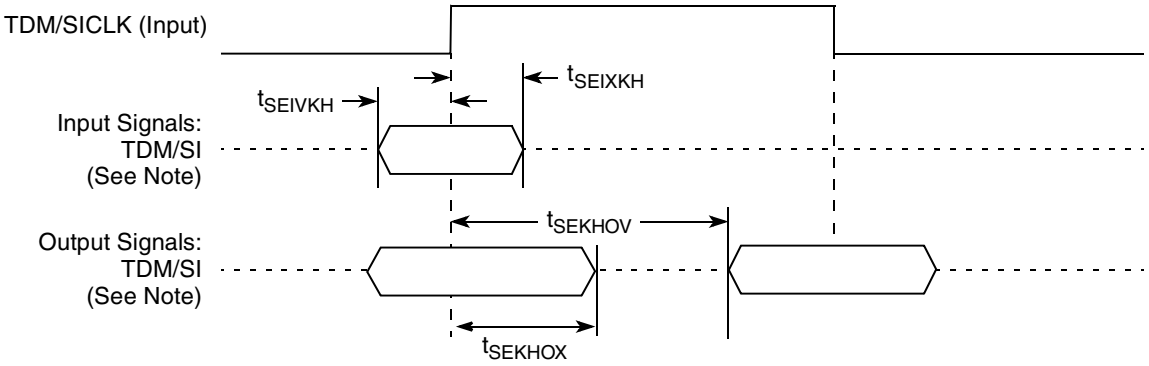


Figure 40. SPI AC Test Load

Figure 44 shows the TDM/SI timing with external clock.



Note: The clock edge is selectable on TDM/SI

Figure 44. TDM/SI AC Timing (External Clock) Diagram

18 UTOPIA/POS

This section describes the DC and AC electrical specifications for the UTOPIA/POS of the MPC8358E.

18.1 UTOPIA/POS DC Electrical Characteristics

Table 58 provides the DC electrical characteristics for the device UTOPIA.

Table 58. UTOPIA DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	0 V ≤ V_{IN} ≤ OV_{DD}	—	±10	µA

18.2 UTOPIA/POS AC Timing Specifications

Table 59 provides the UTOPIA input and output AC timing specifications.

Table 59. UTOPIA AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit	Notes
UTOPIA outputs—Internal clock delay	t_{UIKHOV}	0	11.5	ns	—
UTOPIA outputs—External clock delay	t_{UEKHOV}	1	11.6	ns	—
UTOPIA outputs—Internal clock high impedance	t_{UIKHOX}	0	8.0	ns	—
UTOPIA outputs—External clock high impedance	t_{UEKHOX}	1	10.0	ns	—
UTOPIA inputs—Internal clock input setup time	t_{UIIVKH}	6	—	ns	—

Table 59. UTOPIA AC Timing Specifications[1] (continued)

Characteristic	Symbol[2]	Min	Max	Unit	Notes
UTOPIA inputs—External clock input setup time	t_{UEIVKH}	4.2	—	ns	—
UTOPIA inputs—Internal clock input hold time	t_{UIIXKH}	2.4	—	ns	—
UTOPIA inputs—External clock input hold time	t_{UEIXKH}	1	—	ns	—

Notes:
1. Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{UIKHOX} symbolizes the UTOPIA outputs internal timing (UI) for the time t_{UTOPIA} memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

Figure 45 provides the AC test load for the UTOPIA.

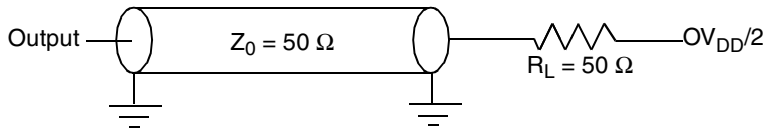


Figure 45. UTOPIA AC Test Load

Figure 46 and Figure 47 represent the AC timing from Table 55. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

Figure 46 shows the UTOPIA timing with external clock.

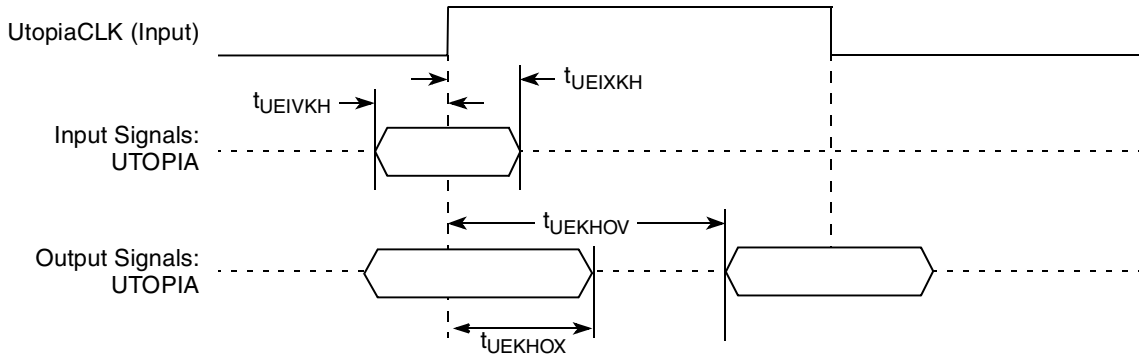


Figure 46. UTOPIA AC Timing (External Clock) Diagram

Table 65. MPC8358E PBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
CE_PA[1:2]	A22, C20	I/O	OV_{DD}	—
CE_PA[3:7]	C3, D3, C2, D2, B1	I/O	$LV_{DD}0$	—
CE_PA[8]	F18	I/O	OV_{DD}	—
CE_PA[9:12]	E3, C1, B2, D1	I/O	$LV_{DD}0$	—
CE_PA[13:14]	B21, D19	I/O	OV_{DD}	—
CE_PA[15]	E4	I/O	$LV_{DD}0$	—
CE_PA[16]	E18	I/O	OV_{DD}	—
CE_PA[17:21]	M2, N5, N3, N4, N2	I/O	$LV_{DD}1$	—
CE_PA[22]	F17	I/O	OV_{DD}	—
CE_PA[23:26]	N1, P1, P2, P4	I/O	$LV_{DD}1$	—
CE_PA[27:28]	A21, E17	I/O	OV_{DD}	—
CE_PA[29]	P5	I/O	$LV_{DD}1$	—
CE_PA[30]	B20	I/O	OV_{DD}	—
CE_PA[31]	M4	I/O	$LV_{DD}1$	—
CE_PB[0:27]	D18, C18, A20, B19, F16, E16, B18, A19, C17, D16, E15, A18, F15, B17, A17, D15, B16, A16, C15, B15, A15, E14, F14, D14, C14, B14, A14, E13	I/O	OV_{DD}	—
CE_PC[0:1]	F13, D13	I/O	OV_{DD}	—
CE_PC[2:3]	N6, M1	I/O	$LV_{DD}1$	—
CE_PC[4:6]	C13, B13, A13	I/O	OV_{DD}	—
CE_PC[7]	R1	I/O	$LV_{DD}2$	—
CE_PC[8:9]	F4, E2	I/O	$LV_{DD}0$	—
CE_PC[10:30]	D12, E12, F12, B12, A12, A11, B11, K5, K6, J1, J2, J3, H1, J4, H6, J5, M5, L1, M3, F5, B22	I/O	OV_{DD}	—
CE_PD[0:27]	H2, H3, G6, G1, H4, H5, G2, G3, F1, J6, F2, G4, E1, G5, B3, A3, D4, C4, A2, E5, B4, F8, A4, D5, C5, B5, E6, E8	I/O	OV_{DD}	—
CE_PE[0:31]	D8, A7, A5, E7, D6, F9, B6, A6, D7, C7, B7, E9, C8, E11, C11, F11, A10, B10, C10, E10, D10, A9, B9, C9, D9, F10, A8, B8, M6, K1, L3, L2	I/O	OV_{DD}	—
CE_PF[0:3]	L6, K2, L5, K4	I/O	OV_{DD}	—
Clocks				
PCI_CLK[0]/ PF[26]	R6	I/O	$LV_{DD}2$	—
PCI_CLK[1:2]/ PF[27:28]	U3, T6	I/O	OV_{DD}	—
CLKIN	AH6	I	OV_{DD}	—
PCI_SYNC_IN	AF7	I	OV_{DD}	—
PCI_SYNC_OUT/ PF[29]	AF6	I/O	OV_{DD}	3
JTAG				
TCK	AD9	I	OV_{DD}	—

22 Clocking

Figure 53 shows the internal distribution of clocks within the MPC8358E.

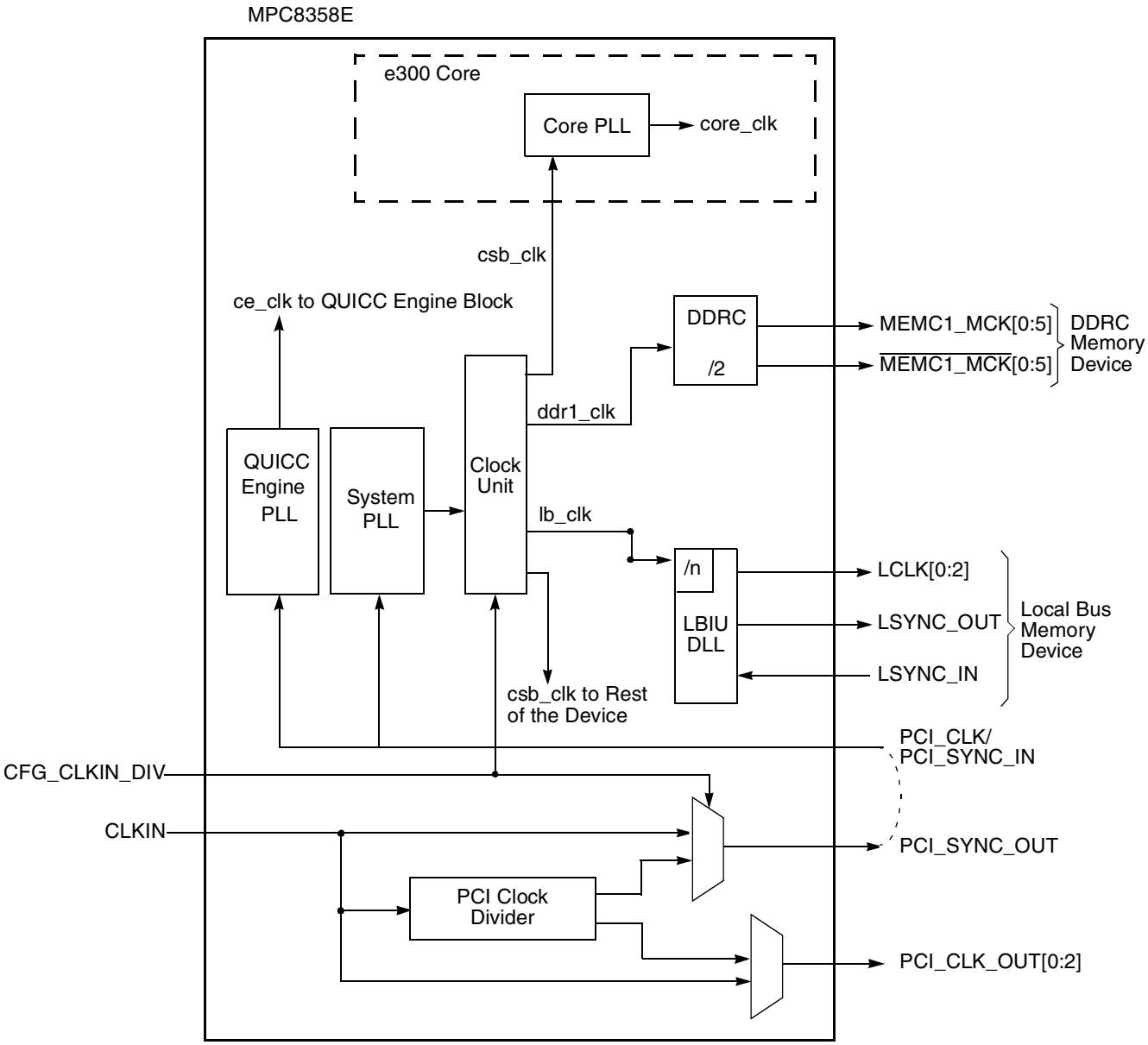


Figure 53. MPC8358E Clock Subsystem

The primary clock source for the device can be one of two inputs, CLKIN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. Note that in PCI host mode, the primary clock input also depends on whether PCI clock outputs are selected with RCWH[PCICKDRV]. When the device is configured as a PCI host device (RCWH[PCIHOST] = 1) and PCI clock output is selected (RCWH[PCICKDRV] = 1), CLKIN is its primary input clock. CLKIN feeds the PCI clock divider (÷2) and the multiplexors for PCI_SYNC_OUT and PCI_CLK_OUT. The CFG_CLKIN_DIV configuration

22.1 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] and RCWL[SVCOD] parameters. Table 68 shows the multiplication factor encodings for the system PLL.

Table 68. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	× 16
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111	× 7
1000	× 8
1001	× 9
1010	× 10
1011	× 11
1100	× 12
1101	× 13
1110	× 14
1111	× 15

The RCWL[SVCOD] denotes the system PLL VCO internal frequency as shown in Table 69.

Table 69. System PLL VCO Divider

RCWL[SVCOD]	VCO Divider
00	4
01	8
10	2
11	Reserved

NOTE

The VCO divider must be set properly so that the system VCO frequency is in the range of 600–1400 MHz.

Table 70. CSB Frequency Options (continued)

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk*: Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			16.67	25	33.33	66.67
			csb_clk Frequency (MHz)			
High	0110	6:1			200	
High	0111	7:1			233	
High	1000	8:1				
High	1001	9:1				
High	1010	10:1				
High	1011	11:1				
High	1100	12:1				
High	1101	13:1				
High	1110	14:1				
High	1111	15:1				
High	0000	16:1				

1 CFG_CLKIN_DIV is only used for host mode; CLKIN must be tied low and CFG_CLKIN_DIV must be pulled down (low) in agent mode.

2 CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.

22.2 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). Table 71 shows the encodings for RCWL[COREPLL]. COREPLL values not listed in Table 71 should be considered reserved.

Table 71. e300 Core PLL Configuration

RCWL[COREPLL]			*core_clk*:*csb_clk* Ratio	VCO divider
0–1	2–5	6		
nn	**0000**	n	PLL bypassed (PLL off, *csb_clk* clocks core directly)	PLL bypassed (PLL off, *csb_clk* clocks core directly)
00	**0001**	0	1:1	÷2
01	**0001**	0	1:1	÷4
10	**0001**	0	1:1	÷8
11	**0001**	0	1:1	÷8
00	**0001**	1	1.5:1	÷2
01	**0001**	1	1.5:1	÷4
10	**0001**	1	1.5:1	÷8

23.2.3 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, the Thermal Characterization Parameter (Ψ_{JT}) can be used to determine the junction temperature with a measurement of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

T_J = junction temperature (°C)
T_T = thermocouple temperature on top of package (°C)
Ψ_{JT} = junction-to-ambient thermal resistance (°C/W)
P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

23.2.4 Heat Sinks and Junction-to-Ambient Thermal Resistance

In some application environments, a heat sink will be required to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction to case thermal resistance and a case to ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

where:

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)
$R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)
$R_{\theta CA}$ = case-to-ambient thermal resistance (°C/W)

$R_{\theta JC}$ is device related and cannot be influenced by the user. The user controls the thermal environment to change the case-to-ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the size of the heat sink, the airflow around the device, the interface material, the mounting arrangement on printed-circuit board, or change the thermal dissipation on the printed-circuit board surrounding the device.

To illustrate the thermal performance of the devices with heat sinks, the thermal performance has been simulated with a few commercially available heat sinks. The heat sink choice is determined by the application environment (temperature, airflow, adjacent component power dissipation) and the physical space available. Because there is not a standard application environment, a standard heat sink is not required.

23.3.1 Experimental Determination of the Junction Temperature with a Heat Sink

When heat sink is used, the junction temperature is determined from a thermocouple inserted at the interface between the case of the package and the interface material. A clearance slot or hole is normally required in the heat sink. Minimizing the size of the clearance is important to minimize the change in thermal performance caused by removing part of the thermal interface to the heat sink. Because of the experimental difficulties with this technique, many engineers measure the heat sink temperature and then back calculate the case temperature using a separate measurement of the thermal resistance of the interface. From this case temperature, the junction temperature is determined from the junction-to-case thermal resistance.

$$T_J = T_C + (R_{\theta JC} \times P_D)$$

where:

T_J = junction temperature (°C)

T_C = case temperature of the package (°C)

$R_{\theta JC}$ = junction to case thermal resistance (°C/W)

P_D = power dissipation (W)

24 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8358E. Additional information can be found in *MPC8360E/MPC8358E PowerQUICC Design Checklist* (AN3097).

24.1 System Clocking

The device includes two PLLs, as follows.

- The platform PLL ($AV_{DD}1$) generates the platform clock from the externally supplied CLKIN input. The frequency ratio between the platform and CLKIN is selected using the platform PLL ratio configuration bits as described in Section 22.1, “System PLL Configuration.”
- The e300 core PLL ($AV_{DD}2$) generates the core clock as a slave to the platform clock. The frequency ratio between the e300 core clock and the platform clock is selected using the e300 PLL ratio configuration bits as described in Section 22.2, “Core PLL Configuration.”

24.2 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins ($AV_{DD}1$, $AV_{DD}2$, respectively). The AV_{DD} level should always be equivalent to V_{DD}, and preferably these voltages will be derived directly from V_{DD} through a low frequency filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide five independent filter circuits as illustrated in Figure 54, one to each of the five AV_{DD} pins. By providing independent filters to each PLL, the opportunity to cause noise injection from one PLL to the other is reduced.

Table 77. Impedance Characteristics (continued)

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI	DDR DRAM	Symbol	Unit
Differential	NA	NA	NA	Z_{DIFF}	W

Note: Nominal supply voltages. See Table 1, T_J = 105°C.

24.6 Configuration Pin Muxing

The device provides the user with power-on configuration options that can be set through the use of external pull-up or pull-down resistors of 4.7 kΩ on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.

While $\overline{\text{HRESET}}$ is asserted however, these pins are treated as inputs. The value presented on these pins while $\overline{\text{HRESET}}$ is asserted, is latched when $\overline{\text{HRESET}}$ deasserts, at which time the input receiver is disabled and the I/O circuit takes on its normal function. Careful board layout with stubless connections to these pull-up/pull-down resistors coupled with the large value of the pull-up/pull-down resistor should minimize the disruption of signal quality or speed for output pins thus configured.

24.7 Pull-Up Resistor Requirements

The device requires high resistance pull-up resistors (10 kΩ is recommended) on open drain type pins including I^2C pins, Ethernet Management MDIO pin, and EPIC interrupt pins.

For more information on required pull-up resistors and the connections required for the JTAG interface, see *MPC8360E/MPC8358E PowerQUICC Design Checklist* (AN3097).

25 Ordering Information

25.1 Part Numbers Fully Addressed by this Document

Table 78 provides the Freescale part numbering nomenclature for the MPC8358E. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. In addition to the processor frequency, the part numbering scheme also